

Attorney's Docket No.: 07977-204002 / US3480D1

a first conductive layer formed on said gate insulating film wherein said first conductive layer extends over said channel region;

a first anodic oxide layer formed on at least side surface of said first conductive layer;

a second conductive layer formed on said first conductive layer; and

a second anodic oxide layer formed on at least side surface of said second conductive layer,

wherein each of said first and second conductive layers comprises a material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt,

wherein an anodization rate of said first conductive layer is greater than that of said second layer so that a width of said first conductive layer is narrower than that of said second conductive layer, and

wherein width between a side edge of said second conductive layer and a side edge of said second anodic oxide layer is 500Å to 1000Å.

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6. [Amended] A semiconductor device comprising:

a semiconductor layer comprising a source region, a drain region, and a channel region formed on an insulating surface;

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a gate insulating film formed on said semiconductor layer;  
a first conductive layer formed on said gate insulating  
film wherein said first conductive layer extends over said  
channel region;

a first anodic oxide layer formed on at least side surface  
of said first conductive layer;

a second conductive layer formed on said first conductive  
layer; and

*F 2*  
*cont.*  
a second anodic oxide layer formed on top and side surface  
of said second conductive layer,

wherein each of said first and second conductive layers  
comprises a material selected from the group consisting of  
molybdenum, tantalum, aluminum, chromium, nickel, zirconium,  
titanium, palladium, silver, copper, and cobalt,

wherein an anodization rate of said first conductive layer  
is greater than that of said second layer so that a width of  
said first conductive layer is narrower than that of said second  
conductive layer, and

wherein width between a side edge of said second conductive  
layer and a side edge of said second anodic oxide layer is 500Å  
to 1000Å.

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11. [Amended] A semiconductor device comprising:

*F 3*  
a semiconductor layer;

a gate insulating film formed on said semiconductor layer;

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a first conductive layer formed on said gate insulating film;

a first anodic oxide layer formed on at least side surface of said first conductive layer;

F3  
Cont.  
a second conductive layer electrically connected to said first conductive layer; and

a second anodic oxide layer formed on at least side surface of said second conductive layer,

wherein said first conductive layer comprises a first material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt,

wherein said second conductive layer comprises a second material which is different from said first material,

wherein a width of said first conductive layer is narrower than that of said second conductive layer, and

wherein width between a side edge of said second conductive layer and a side edge of said second anodic oxide layer is 500Å to 1000Å.

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16. [Amended] A semiconductor device comprising:

F4  
a semiconductor layer;

a gate insulating film formed on said semiconductor layer;

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a first conductive layer formed on said gate insulating film;

a first anodic oxide layer formed on at least side surface of said first conductive layer;

a second conductive layer electrically connected to said first conductive layer wherein said first conductive layer comprises a different material from said first conductive layer; and

*F<sup>4</sup>* a second anodic oxide layer formed on top and side surface of said second conductive layer,

wherein said first conductive layer comprises a first material selected from the group consisting of molybdenum, tantalum, aluminum, chromium, nickel, zirconium, titanium, palladium, silver, copper, and cobalt,

wherein said second conductive layer comprises a second material which is different from said first material,

wherein a width of said first conductive layer is narrower than that of said second conductive layer,

wherein said insulating film is formed on side surfaces of said first and second conductive layers and a top surface of said second conductive layer, and

wherein width between a side edge of said second conductive layer and a side edge of said second anodic oxide layer is 500Å to 1000Å.

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21. [Amended] A semiconductor device comprising:  
a semiconductor layer comprising a source region, a drain  
region, and a channel region formed over an insulating surface;  
a gate insulating film formed over said semiconductor  
layer,  
*F5*  
a gate electrode comprising a first conductive layer formed  
on [an insulating surface] said gate insulating film and a  
second conductive layer formed on said first conductive layer;  
a first anodic oxide layer formed on side surface of said  
first conductive layer; and  
a second anodic oxide layer formed on top and side surface  
of said second conductive layer,  
wherein said second conductive layer comprises a second  
material which is different from said first material, [and]  
wherein a width of said second conductive layer is narrower  
than that of said first conductive layer, and  
wherein width between a side edge of said second conductive  
layer and a side edge of said second anodic oxide layer is 500Å  
to 1000Å.

Please add the following new claims 39-43.

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39. [New] A semiconductor device according to claim 1,  
wherein said width is larger than a thickness of said first  
conductive layer.

F6  
40. [New] A semiconductor device according to claim 6,  
wherein said width is larger than a thickness of said first  
conductive layer.

41. [New] A semiconductor device according to claim 11,  
wherein said width is larger than a thickness of said first  
conductive layer.

42. [New] A semiconductor device according to claim 16,  
wherein said width is larger than a thickness of said first  
conductive layer.

43. [New] A semiconductor device according to claim 21,  
wherein said width is larger than a thickness of said first  
conductive layer.